

U.S. Application Serial No.: 10/725,801
Amendment Dated March 22, 2005
In Response to Office Action Dated December 23, 2004

Amendments to the Claims

This listing will replace all prior versions and listings of claims in the application:

Listing of Claims

1. (currently amended) A semiconductor diode with hydrogen detection capability, comprising:

a semiconductor substrate;

a doped semiconductor active layer formed on said substrate and made from a compound having the formula XYZ, in which X is a Group III element, Y is another Group III element different from X, and Z is a Group V element;

an ohmic contact layer formed on said active layer; and

a Schottky barrier contact layer formed on said active layer so as to provide a Schottky barrier therebetween, said Schottky barrier contact layer being made from a metal that is capable of dissociating a hydrogen molecule into hydrogen atoms; and

an oxide layer sandwiched between said active layer and said Schottky barrier contact layer.

2. (cancelled)

3. (currently amended) The semiconductor diode of Claim 12, wherein said oxide layer has a thickness ranging from 20 to 500 Å.

4. (original) The semiconductor diode of Claim 1, wherein said compound of said active layer is selected from the group consisting of n-type InGaP and $\text{Al}_x\text{Ga}_{1-x}\text{As}$.

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5. (original) The semiconductor diode of Claim 1, wherein said compound of said active layer is n-type InGaP with a dopant concentration ranging from 1×10^{16} to 5×10^{17} atoms/cm³, said active layer having a thickness ranging from 1000 to 50000Å.

6. (original) The semiconductor diode of Claim 1, wherein said compound of said active layer is $\text{Al}_x\text{Ga}_{1-x}\text{As}$ with $x=0-1$ and a dopant concentration ranging from 1×10^{16} to 5×10^{17} atoms/cm³, said active layer having a thickness ranging from 1000 to 50000Å.

7. (original) The semiconductor diode of Claim 1, further comprising a semiconductor buffer layer sandwiched between said substrate and said active layer.

8. (original) The semiconductor diode of Claim 7, wherein said buffer layer is made from undoped GaAs and has a thickness ranging from 1000 to 50000 Å.

9. (original) The semiconductor diode of Claim 1, wherein said substrate is made from semi-insulating GaAs.

10. (original) The semiconductor diode of Claim 1, wherein said ohmic contact layer is made from AuGe/Ni and has a thickness ranging from 1000 to 50000Å.

11. (original) The semiconductor diode of Claim 1, wherein said ohmic contact layer is made from AuGe and has a thickness ranging from 1000 to 50000Å.

12. (original) The semiconductor diode of Claim 1, wherein said metal of said Schottky barrier contact layer is selected from the group consisting of Pt, Pd, Ni, Rh,

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13. (original) The semiconductor diode of Claim 1, wherein said Schottky barrier contact layer has a thickness ranging from 1000 to 20000Å.